

# General Purpose Transistor

## NPN Silicon

# MPS3904

### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	$V_{CEO}$	40	Vdc
Collector-Base Voltage	$V_{CBO}$	60	Vdc
Emitter-Base Voltage	$V_{EBO}$	6.0	Vdc
Collector Current — Continuous	$I_C$	100	mA dc
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	625 5.0	mW mW/ $^\circ\text{C}$
Total Power Dissipation @ $T_A = 60^\circ\text{C}$	$P_D$	450	mW
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	1.5 12	Watts mW/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$

### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	$^\circ\text{C/W}$
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	$^\circ\text{C/W}$

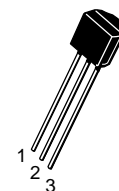
### ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
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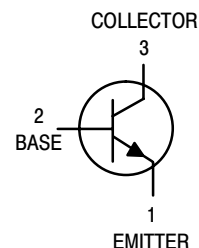
### OFF CHARACTERISTICS

Collector-Emitter Breakdown Voltage <sup>(1)</sup> ( $I_C = 1.0 \text{ mA dc}, I_B = 0$ )	$V_{(BR)CEO}$	40	—	Vdc
Collector-Base Breakdown Voltage ( $I_C = 10 \mu\text{A dc}, I_E = 0$ )	$V_{(BR)CBO}$	60	—	Vdc
Emitter-Base Breakdown Voltage ( $I_E = 10 \mu\text{A dc}, I_C = 0$ )	$V_{(BR)EBO}$	6.0	—	Vdc
Collector Cutoff Current ( $V_{CE} = 30 \text{ Vdc}, V_{EB(off)} = 3.0 \text{ Vdc}$ )	$I_{CEX}$	—	50	nA dc
Base Cutoff Current ( $V_{CE} = 30 \text{ Vdc}, V_{EB(off)} = 3.0 \text{ Vdc}$ )	$I_{BL}$	—	50	nA dc

1. Pulse Test: Pulse Width  $\leq 300 \mu\text{s}$ , Duty Cycle  $\leq 2.0\%$ .



CASE 29-04, STYLE 1  
TO-92 (TO-226AA)



**ELECTRICAL CHARACTERISTICS** ( $T_A = 25^\circ\text{C}$  unless otherwise noted) (Continued)

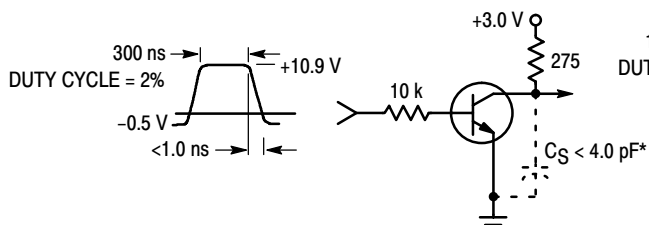
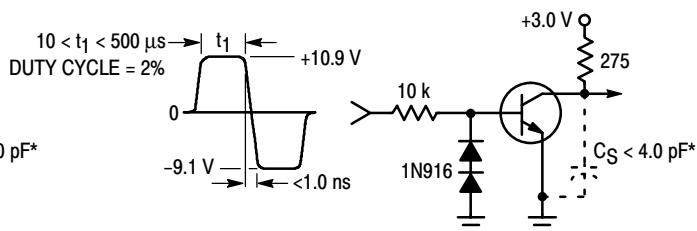
Characteristic	Symbol	Min	Max	Unit
<b>ON CHARACTERISTICS(1)</b>				
DC Current Gain ( $I_C = 0.1\text{ mA}$ , $V_{CE} = 1.0\text{ Vdc}$ ) ( $I_C = 1.0\text{ mA}$ , $V_{CE} = 1.0\text{ Vdc}$ ) ( $I_C = 10\text{ mA}$ , $V_{CE} = 1.0\text{ Vdc}$ ) ( $I_C = 50\text{ mA}$ , $V_{CE} = 1.0\text{ Vdc}$ ) ( $I_C = 100\text{ mA}$ , $V_{CE} = 1.0\text{ Vdc}$ )	$h_{FE}$	40 70 100 60 30	— — 300 — —	—
Collector–Emitter Saturation Voltage ( $I_C = 10\text{ mA}$ , $I_B = 1.0\text{ mA}$ ) ( $I_C = 50\text{ mA}$ , $I_B = 5.0\text{ mA}$ )	$V_{CE(sat)}$	— —	0.2 0.3	Vdc
Base–Emitter Saturation Voltage ( $I_C = 10\text{ mA}$ , $I_B = 1.0\text{ mA}$ ) ( $I_C = 50\text{ mA}$ , $I_B = 5.0\text{ mA}$ )	$V_{BE(sat)}$	0.65 —	0.85 1.1	Vdc

**SMALL–SIGNAL CHARACTERISTICS**

Current–Gain — Bandwidth Product ( $I_C = 10\text{ mA}$ , $V_{CE} = 20\text{ Vdc}$ , $f = 100\text{ MHz}$ )	$f_T$	300	—	MHz
Output Capacitance ( $V_{CB} = 5.0\text{ Vdc}$ , $I_E = 0$ , $f = 1.0\text{ MHz}$ )	$C_{obo}$	—	4.0	pF
Input Capacitance ( $V_{EB} = 0.5\text{ Vdc}$ , $I_C = 0$ , $f = 1.0\text{ MHz}$ )	$C_{ibo}$	—	8.0	pF
Input Impedance ( $I_C = 1.0\text{ mA}$ , $V_{CE} = 10\text{ Vdc}$ , $f = 1.0\text{ kHz}$ )	$h_{ie}$	1.0	10	k $\Omega$
Voltage Feedback Ratio ( $I_C = 1.0\text{ mA}$ , $V_{CE} = 10\text{ Vdc}$ , $f = 1.0\text{ kHz}$ )	$h_{re}$	0.5	8.0	$\times 10^{-4}$
Small–Signal Current Gain ( $I_C = 1.0\text{ mA}$ , $V_{CE} = 10\text{ Vdc}$ , $f = 1.0\text{ kHz}$ )	$h_{fe}$	100	400	—
Output Admittance ( $I_C = 1.0\text{ mA}$ , $V_{CE} = 10\text{ Vdc}$ , $f = 1.0\text{ kHz}$ )	$h_{oe}$	1.0	40	$\mu\text{mhos}$
Noise Figure ( $I_C = 100\text{ }\mu\text{A}$ , $V_{CE} = 5.0\text{ Vdc}$ , $R_S = 1.0\text{ k}\Omega$ , $f = 1.0\text{ kHz}$ )	NF	—	5.0	dB

**SWITCHING CHARACTERISTICS**

Delay Time	(V <sub>CC</sub> = 3.0 Vdc, V <sub>BE(off)</sub> = –0.5 Vdc, I <sub>C</sub> = 10 mA, I <sub>B1</sub> = 1.0 mA)	t <sub>d</sub>	—	35	ns
Rise Time		t <sub>r</sub>	—	50	ns
Storage Time	(V <sub>CC</sub> = 3.0 Vdc, I <sub>C</sub> = 10 mA, I <sub>B1</sub> = I <sub>B2</sub> = 1.0 mA)	t <sub>s</sub>	—	900	ns
Fall Time		t <sub>f</sub>	—	90	ns

1. Pulse Test: Pulse Width  $\leq 300\text{ }\mu\text{s}$ , Duty Cycle  $\leq 2.0\%$ .**EQUIVALENT SWITCHING TIME TEST CIRCUITS****Figure 1. Turn–On Time****Figure 2. Turn–Off Time**

\*Total shunt capacitance of test jig and connectors

# TYPICAL NOISE CHARACTERISTICS

( $V_{CE} = 5.0 \text{ Vdc}$ ,  $T_A = 25^\circ\text{C}$ )

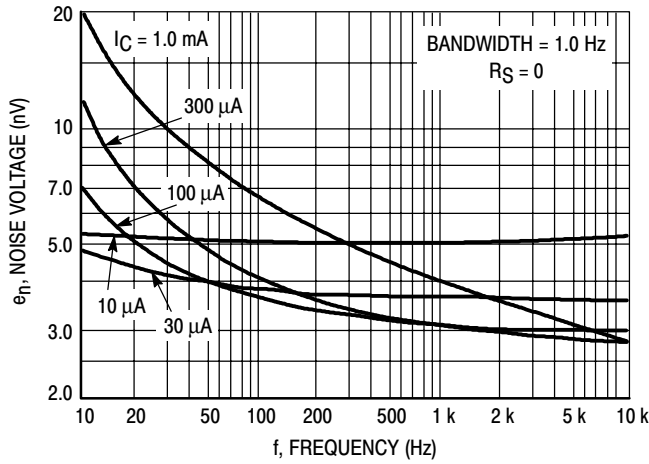


Figure 3. Noise Voltage

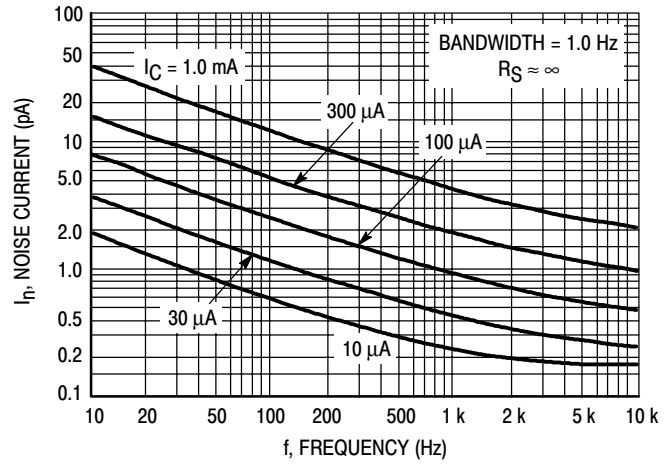


Figure 4. Noise Current

## NOISE FIGURE CONTOURS

( $V_{CE} = 5.0 \text{ Vdc}$ ,  $T_A = 25^\circ\text{C}$ )

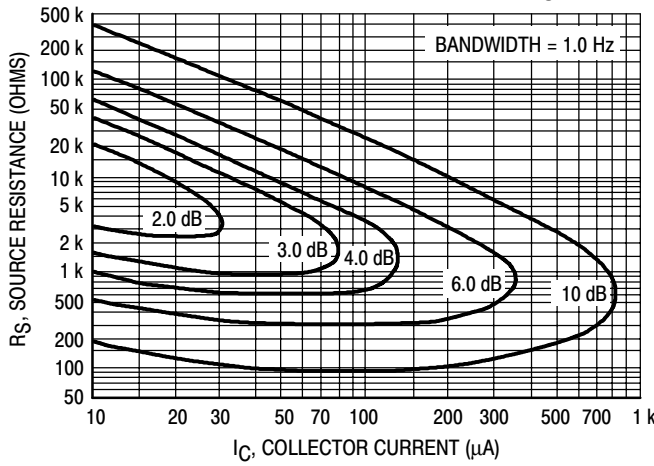


Figure 5. Narrow Band, 100 Hz

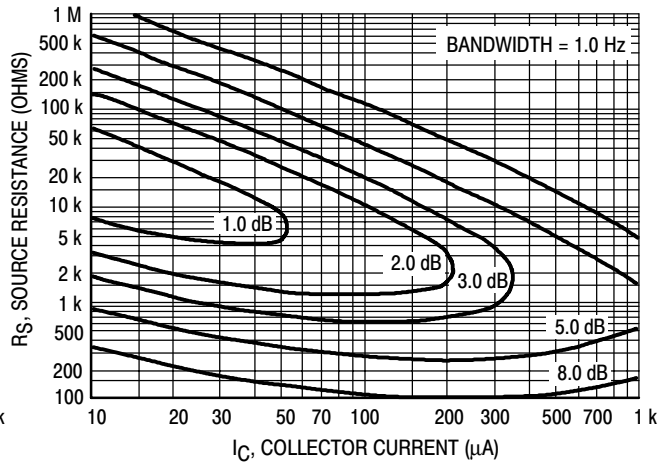


Figure 6. Narrow Band, 1.0 kHz

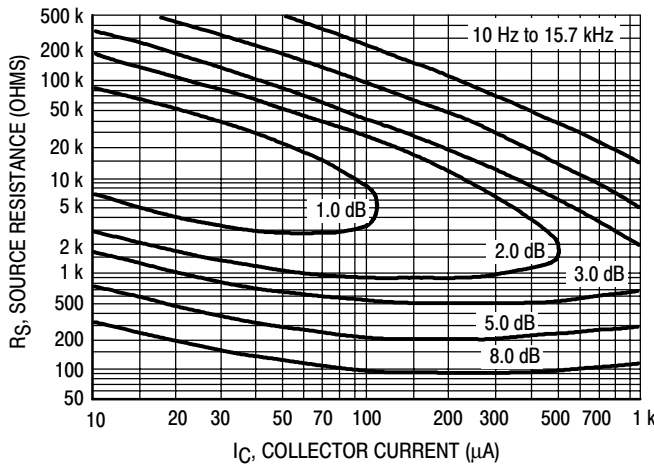


Figure 7. Wideband

Noise Figure is defined as:

$$NF = 20 \log_{10} \left( \frac{e_n^2 + 4KTR_S + I_n^2 R_S^2}{4KTR_S} \right)^{1/2}$$

$e_n$  = Noise Voltage of the Transistor referred to the input. (Figure 3)

$I_n$  = Noise Current of the Transistor referred to the input. (Figure 4)

$K$  = Boltzman's Constant ( $1.38 \times 10^{-23} \text{ J/}^\circ\text{K}$ )

$T$  = Temperature of the Source Resistance ( $^\circ\text{K}$ )

$R_S$  = Source Resistance (Ohms)

# MPS3904

## TYPICAL STATIC CHARACTERISTICS

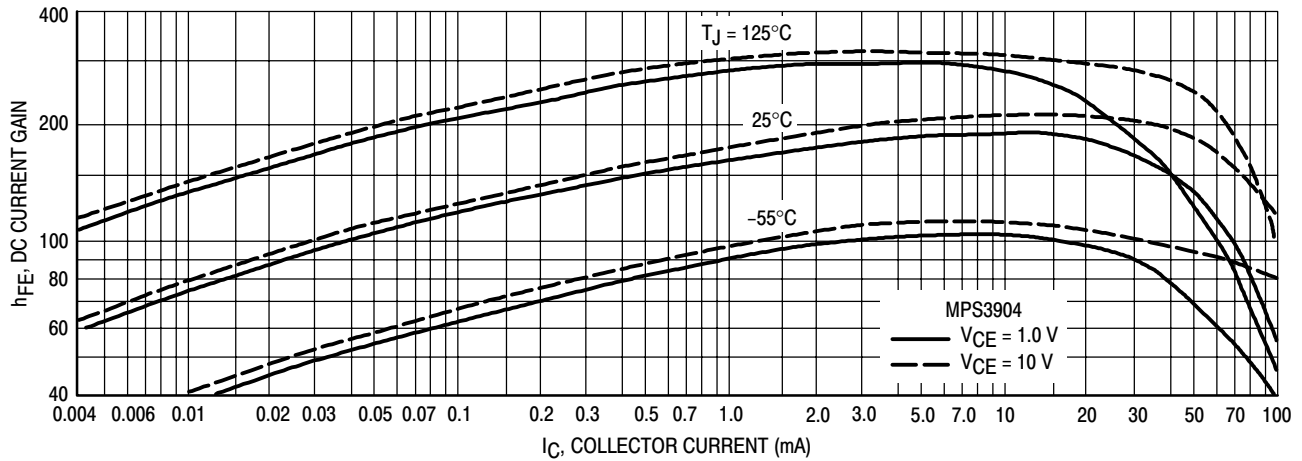


Figure 8. DC Current Gain

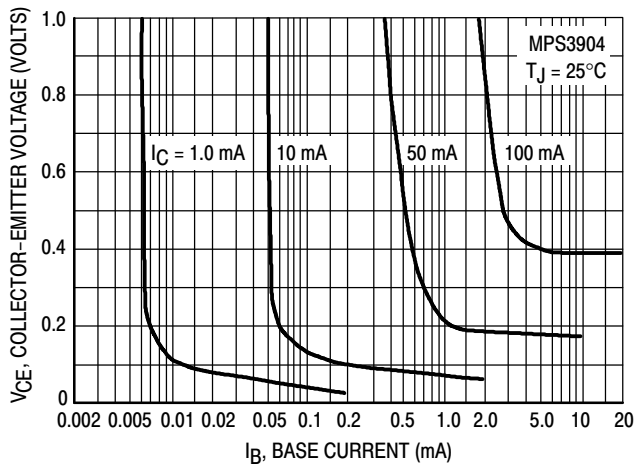


Figure 9. Collector Saturation Region

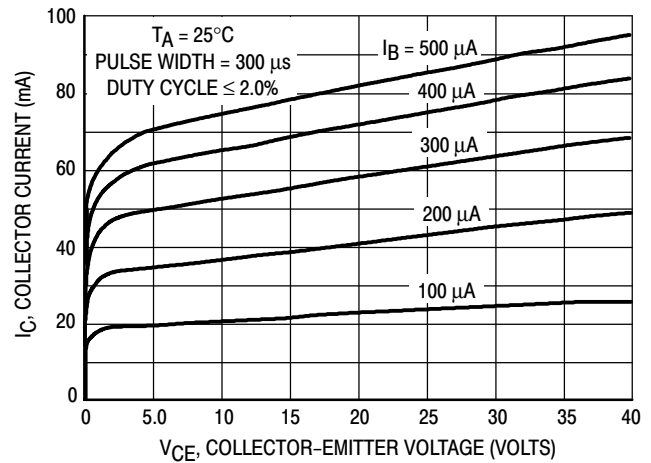


Figure 10. Collector Characteristics

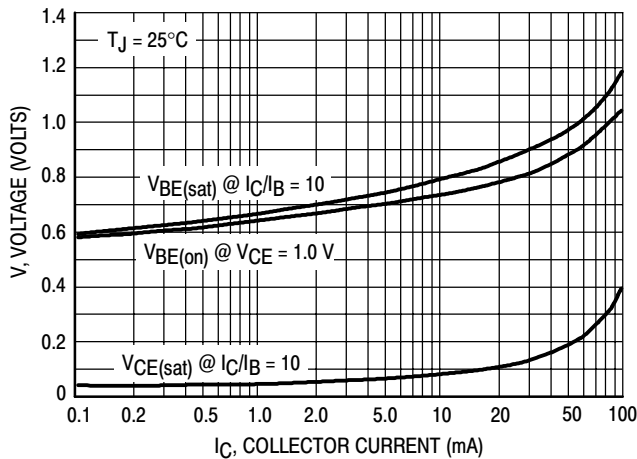


Figure 11. "On" Voltages

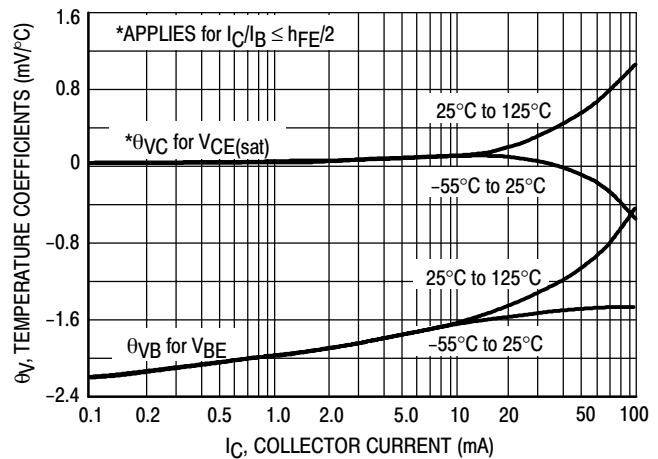


Figure 12. Temperature Coefficients

TYPICAL DYNAMIC CHARACTERISTICS

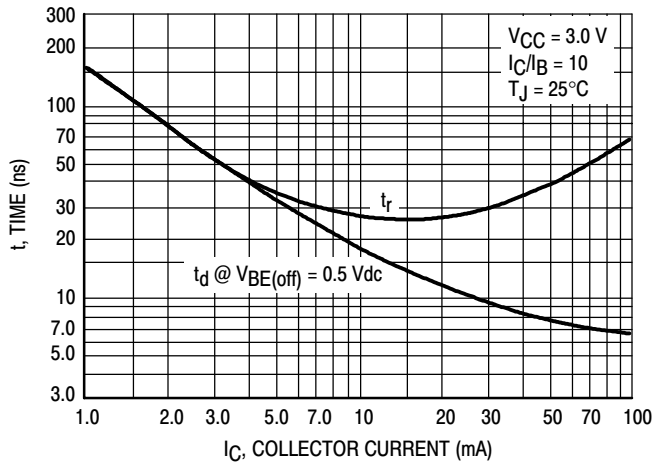


Figure 13. Turn-On Time

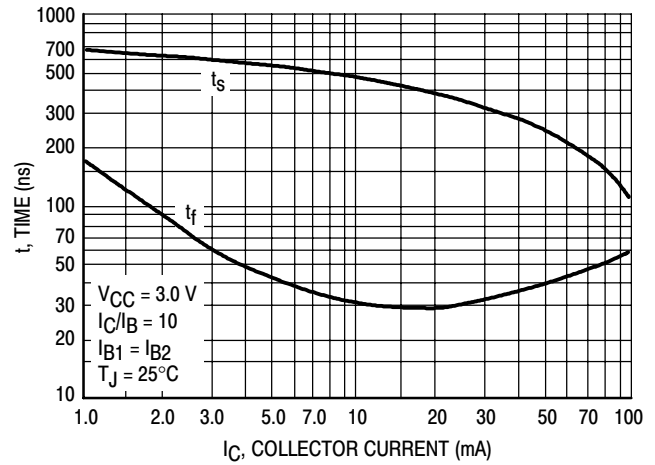


Figure 14. Turn-Off Time

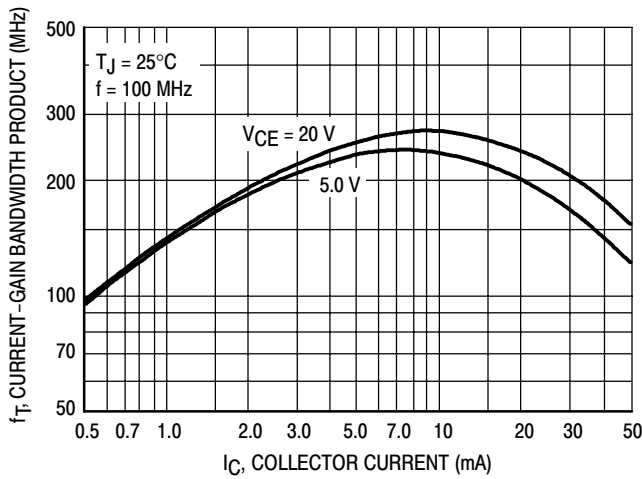


Figure 15. Current-Gain — Bandwidth Product

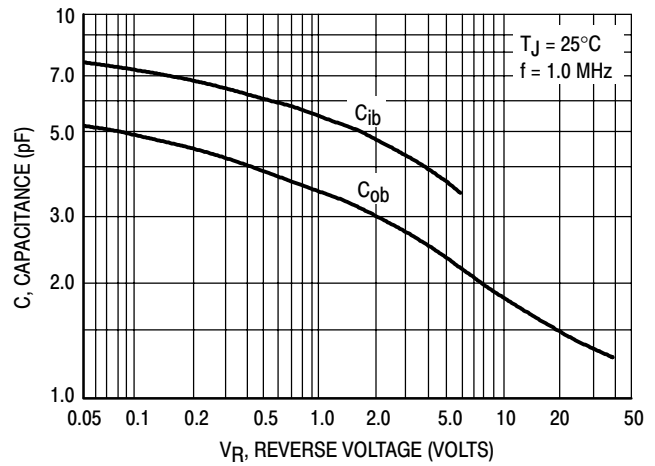


Figure 16. Capacitance

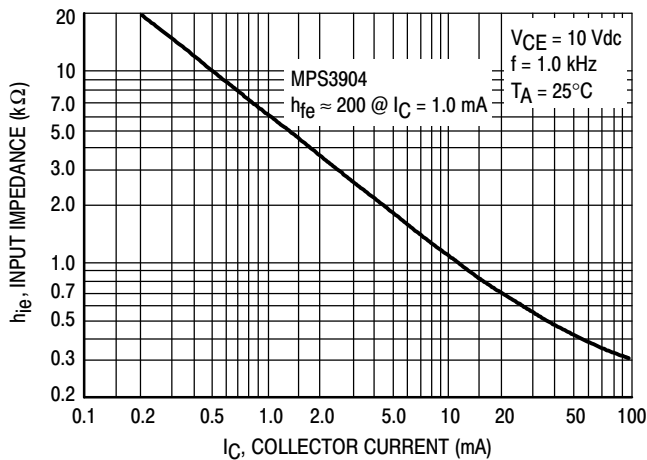


Figure 17. Input Impedance

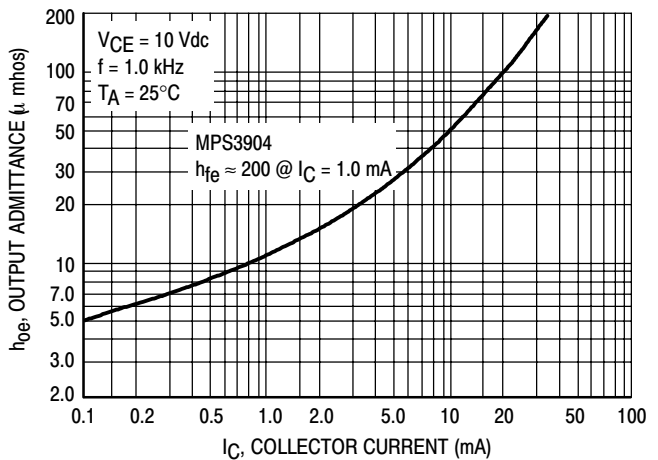


Figure 18. Output Admittance

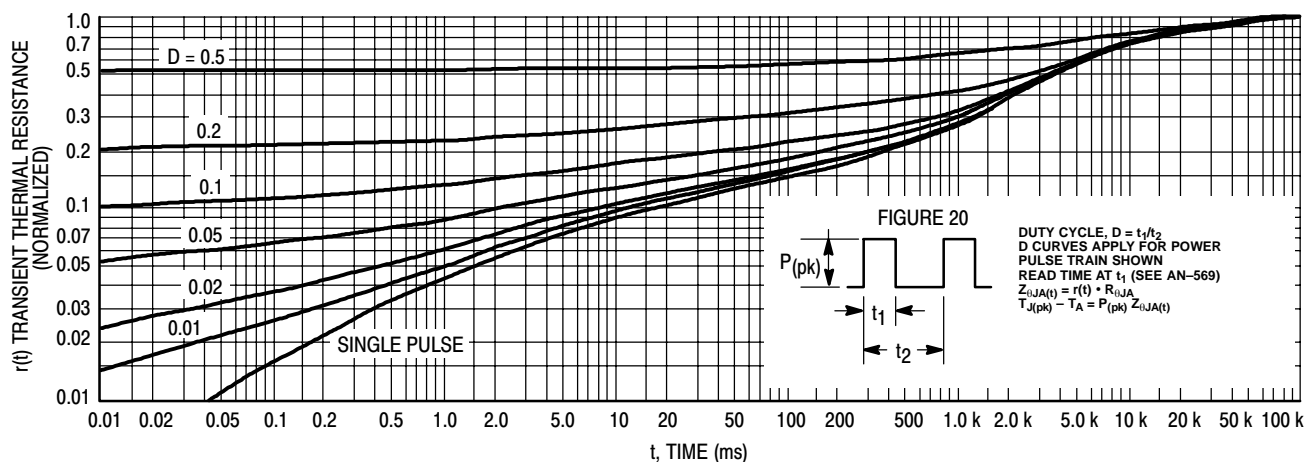


Figure 19. Thermal Response

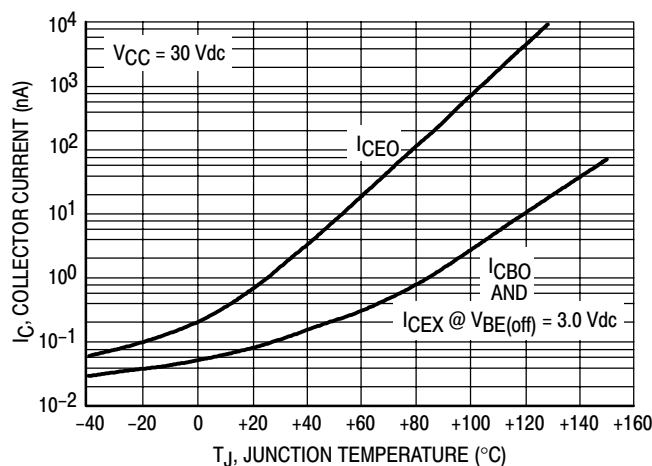


Figure 21.

#### DESIGN NOTE: USE OF THERMAL RESPONSE DATA

A train of periodical power pulses can be represented by the model as shown in Figure 20. Using the model and the device thermal response the normalized effective transient thermal resistance of Figure 19 was calculated for various duty cycles.

To find  $Z_{\theta JA}(t)$ , multiply the value obtained from Figure 19 by the steady state value  $R_{\theta JA}$ .

Example:

The MPS3904 is dissipating 2.0 watts peak under the following conditions:

$t_1 = 1.0$  ms,  $t_2 = 5.0$  ms. ( $D = 0.2$ )

Using Figure 19 at a pulse width of 1.0 ms and  $D = 0.2$ , the reading of  $r(t)$  is 0.22.

The peak rise in junction temperature is therefore

$$\Delta T = r(t) \times P(pk) \times R_{\theta JA} = 0.22 \times 2.0 \times 200 = 88^\circ\text{C}.$$

For more information, see ON Semiconductor Application Note AN569/D, available from the Literature Distribution Center or on our website at [www.onsemi.com](http://www.onsemi.com).

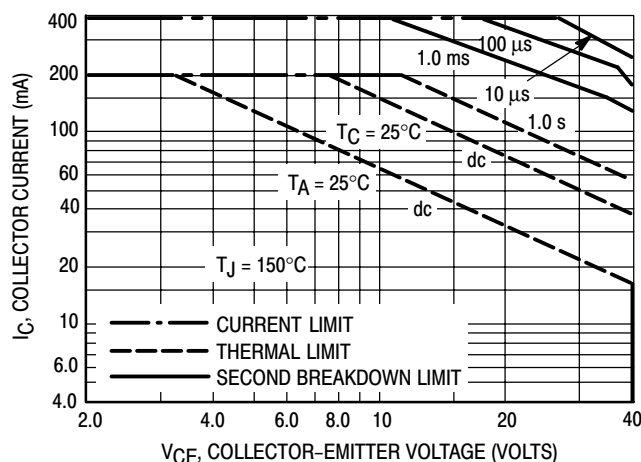


Figure 22.

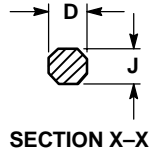
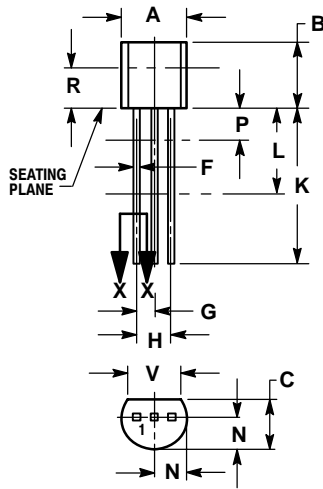
The safe operating area curves indicate  $I_C$ - $V_{CE}$  limits of the transistor that must be observed for reliable operation. Collector load lines for specific circuits must fall below the limits indicated by the applicable curve.

The data of Figure 22 is based upon  $T_{J(pk)} = 150^\circ\text{C}$ ;  $T_C$  or  $T_A$  is variable depending upon conditions. Pulse curves are valid for duty cycles to 10% provided  $T_{J(pk)} \leq 150^\circ\text{C}$ .  $T_{J(pk)}$  may be calculated from the data in Figure 19. At high case or ambient temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

# MPS3904

## PACKAGE DIMENSIONS

CASE 029-04  
(TO-226AA)  
ISSUE AD




### NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. DIMENSION F APPLIES BETWEEN P AND L. DIMENSION D AND J APPLY BETWEEN L AND K. MINIMUM. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.175	0.205	4.45	5.20
B	0.170	0.210	4.32	5.33
C	0.125	0.165	3.18	4.19
D	0.016	0.022	0.41	0.55
F	0.016	0.019	0.41	0.48
G	0.045	0.055	1.15	1.39
H	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500	---	12.70	---
L	0.250	---	6.35	---
N	0.080	0.105	2.04	2.66
P	---	0.100	---	2.54
R	0.115	---	2.93	---
V	0.135	---	3.43	---

### STYLE 1:

1. EMITTER
2. BASE
3. COLLECTOR

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